

In the Abstract

Please delete the Abstract and replace with the following:

A transistor structure which includes a raised source, a raised drain, a gate located between the source and the drain, a first capping layer in communication with at least a portion of the gate and the source, a second capping layer in communication with at least a portion of the gate and the drain, a first portion of a gate oxide region in communication with at least a portion of the gate and the source, a second portion of a gate oxide region in communication with at least a portion of the gate and the drain. The source, the gate, the first capping layer, and the first portion of a gate oxide region define a first gap. The drain, the gate, the second capping layer, and the second portion of a gate oxide region define a second gap. The structure also includes a first junction area located beneath the first gap, the gate and the source and a second junction area located beneath the second gap, the gate and the drain.

REMARKS

Attached to this amendment and response to office action is a document titled "Version With Markings To Show Changes Made", which illustrates the deletions and additions that were made to the specification, abstract, and claims herein.

Abstract

Applicants have herein amended the Abstract to conform to the claims of the instant application.